

Charge Redistribution in NiSe₂/MoS₂ n–n Heterojunction towards the Photoelectrocatalytic Degradation of Ciprofloxacin

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This study reports the photoelectrocatalytic (PEC) activity of a n–n heterojunction comprising MoS₂ and NiSe₂. The synthesis of the composite was achieved through a facile solvothermal method, yielding an exfoliated MoS₂ layered sheet loaded with NiSe₂ nanoparticles. Under visible light radiation and an external electric field, the obtained composite NiSe₂/MoS₂ exhibited enhanced catalytic activity for ciprofloxacin (CIP) degradation. The NiSe₂/MoS₂ heterojunction achieved about 78% degradation efficiency with a first-order kinetic rate of 0.0111 min⁻¹, compared to 38% efficiency and a first-order kinetic rate of 0.0044 min⁻¹ observed for MoS₂. The NiSe₂/MoS₂ heterojunction was more advantageous due to the synergy of charge carrier induction by visible light radiation and improved

charge carrier separation induced by the external electric field. The formation of n–n heterojunction at the interface of the two materials resulted in charge redistribution in the materials, with a simultaneous realignment of the band structure to achieve Fermi energy equilibration. The primary reactive species responsible for CIP degradation was identified as the photo-induced h⁺. Furthermore, the catalyst exhibited high stability and reusability, with no significant reduction in activity observed after five experimental cycles. This study reveals the potential of exploring the synergy between the photocatalytic and electrocatalytic processes in removing harmful pharmaceutical compounds from water.

Introduction

The pollution of aquatic systems by pharmaceutical substances has become a significant issue in environmental sustainability and public health.^[1] Among these pollutants, ciprofloxacin, a widely used antibiotic, poses significant challenges due to its persistence and potential adverse effects on aquatic ecosystems and human health.^[2] To address this issue, advanced oxidation processes (AOPs) have garnered attention for their effectiveness in degrading pharmaceutical compounds.^[3] Among AOPs, photoelectrocatalysis (PEC) stands out as a promising technique that combines the advantages of photocatalysis and electrocatalysis, offering enhanced pollutant degradation under visible light irradiation and efficient charge separation.^[4]

An essential requirement for a PEC process is the development of a photoanode with high efficiency in trapping light energy for the generation and transmission of charge carriers for the degradation process.^[5] As a characteristic 2D layered material, MoS₂ has been extensively applied in optoelectronic devices and semiconductor photocatalysis because of its high charge carrier mobility and excellent optical absorption characteristics.^[6] However, rapid photogenerated charge carrier recombination, limited active sites, and laborious catalyst separation and recycling hinder its practical application.^[7] A significant challenge with MoS₂ is that the active sites are at the edge due to the S–Mo–S coordination of its crystals, forming unsaturated Mo and S atoms only at the edge.^[8] Therefore, several techniques have been explored to improve the catalytic activity of MoS₂, the most explored being the formation of heterostructure with other semiconductor materials such as MoS₂/C₃N₄,^[9] MoS₂-Bi₂WO₆,^[10] ZnIn₂S₄/MoS₂^[11] and TiO₂-MoS₂.^[12] The layered structure of MoS₂ makes it suitable for the formation of heterostructure, and its properties can also be significantly altered by varying the thickness of the material.^[13] To mitigate the challenge of rapid charge carrier recombination, which is the most significant limitation of MoS₂ in its application as a photoanode, three different heterojunction schemes have been identified: type II, Z-scheme, and S-scheme heterojunction. The inherent limitations of type II and Z-scheme heterojunctions, such as the weakening of charge carrier potentials and the hampering of the charge transition process by undesired side redox reaction, restrict their potential in enhancing charge carrier separation in semiconductor heterojunctions.^[14]

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The excellent electronic properties of NiSe₂ have attracted significant attention in several applications, such as dye-sensitized solar cells, hydrogen production, and sodium-ion batteries, because of its high-power conversion efficiency, low overpotential, and high discharge capacity.^[15] Given the electronic properties and the potential of NiSe₂, it could be a suitable co-catalyst for creating an n-n-type heterojunction with improved activity for PEC.

This study reports the PEC performance of NiSe₂/MoS₂ heterojunction. The n-n-type heterojunction took advantage of improved charge carrier separation and transport, and the PEC process's external potential in enhancing the material's PEC performance. The insights from this study highlight the benefits of heterostructure engineering for developing functional materials aimed at environmental remediation. Furthermore, the potential application of this material in photoelectrochemical (PEC) technology for water treatment is demonstrated, addressing the challenges posed by pharmaceutical contaminants like ciprofloxacin in aquatic environments.

Results and Discussion

Structure and Morphology

The NiSe₂ was prepared by a facile solvothermal synthesis, while the NiSe₂/MoS₂ composite was prepared by introducing MoS₂ into the solvothermal process. The crystal structure and morphology of the MoS₂ and NiSe₂/MoS₂ were studied by X-ray diffraction and transmission electron microscopy (TEM), as shown in Figure 1. The XRD pattern of MoS₂ (Figure 1a) showed a pattern characteristic of hexagonal MoS₂, with *P63/mmc* space group in reference to the JCPDS card no. 37-1492.^[16] The high intensity of the peak at $2\theta = 14.3^\circ$, which corresponds to the (002) phase of MoS₂, shows the high thickness of the MoS₂ and

suggests a multilayered MoS₂ sheet. The peaks associated with the NiSe₂ could not be seen due to the low concentration. The XRD spectra of NiSe₂/MoS₂ were similar to that of MoS₂; however, the weakening of the 002 phase peak suggests the exfoliation of the MoS₂ into few-layered MoS₂ due to the incorporation of NiSe₂ onto the MoS₂ sheet.^[16b] The SEM images of MoS₂ and NiSe₂/MoS₂ (Figure 1b&c) show the morphological difference between MoS₂ and NiSe₂/MoS₂. The multilayered nature of MoS₂ and the partial exfoliation of MoS₂ in NiSe₂/MoS₂ can be observed. This exfoliation could be attributed to the solvothermal treatment the MoS₂ sheet was subjected to during the heterojunction formation. The exfoliation of MoS₂ has been reported to play a significant role in its effectiveness as a photocatalytic material.^[17] The TEM images of MoS₂ and NiSe₂/MoS₂ (Figure 1d&e) support the SEM images' observation. The exfoliation of MoS₂ in NiSe₂/MoS₂ could be seen in the TEM image, while the deposition of NiSe₂ nanoparticles on the exfoliated sheets could be vividly observed.

XPS analysis was carried out to investigate the chemical composition and valence state of the samples. The overall survey spectrum of MoS₂ and NiSe₂/MoS₂ (Figure 2a&b) indicates the existence of Mo, S, Ni, and Se elements. The high-resolution XPS spectra of Mo 3d, S 2p, Ni 2p and Se 3d in MoS₂ and NiSe₂/MoS₂ were also compared. The spectra of MoS₂ (Figure 2c) exhibited two prominent peaks at 229.23 and 232.5 eV, which are due to the Mo⁴⁺ 3d_{5/2} and Mo⁴⁺ 3d_{3/2} components of MoS₂. A peak observed at 226.5 eV is attributed to the S 2s of MoS₂. The binding energy region of Mo 3d and S 2p shows that the MoS₂ possesses a robust trigonal prismatic configuration.^[18] In the spectra of NiSe₂/MoS₂, the doublet Mo⁴⁺ and S 2s peaks showed a slight shift to higher binding energy. The Mo⁴⁺ 3d_{5/2} and Mo⁴⁺ 3d_{3/2} peaks shifted to 236.34 and 233.16 eV, respectively. This shift suggests a flow of electron from MoS₂ to NiSe₂ after the formation of the NiSe₂/MoS₂ heterojunction.^[19] However, a small new peak located at

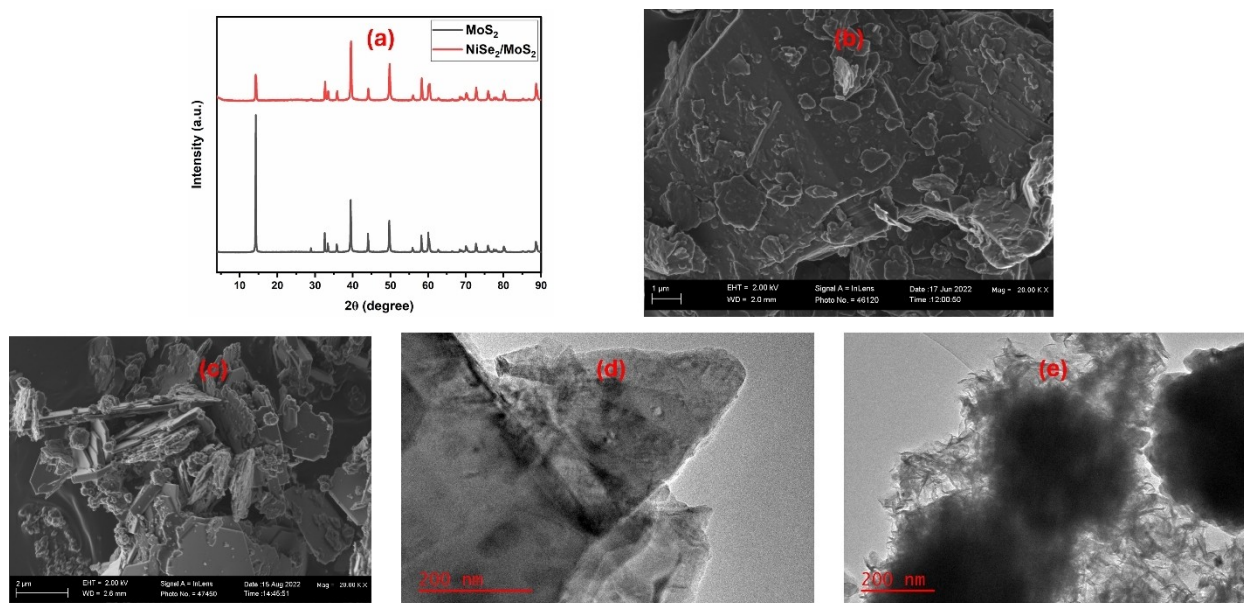


Figure 1. (a) XRD spectra of MoS₂ and NiSe₂/MoS₂, (b & c) SEM images of MoS₂ and NiSe₂/MoS₂ and (d & e) TEM images of MoS₂ and NiSe₂/MoS₂.

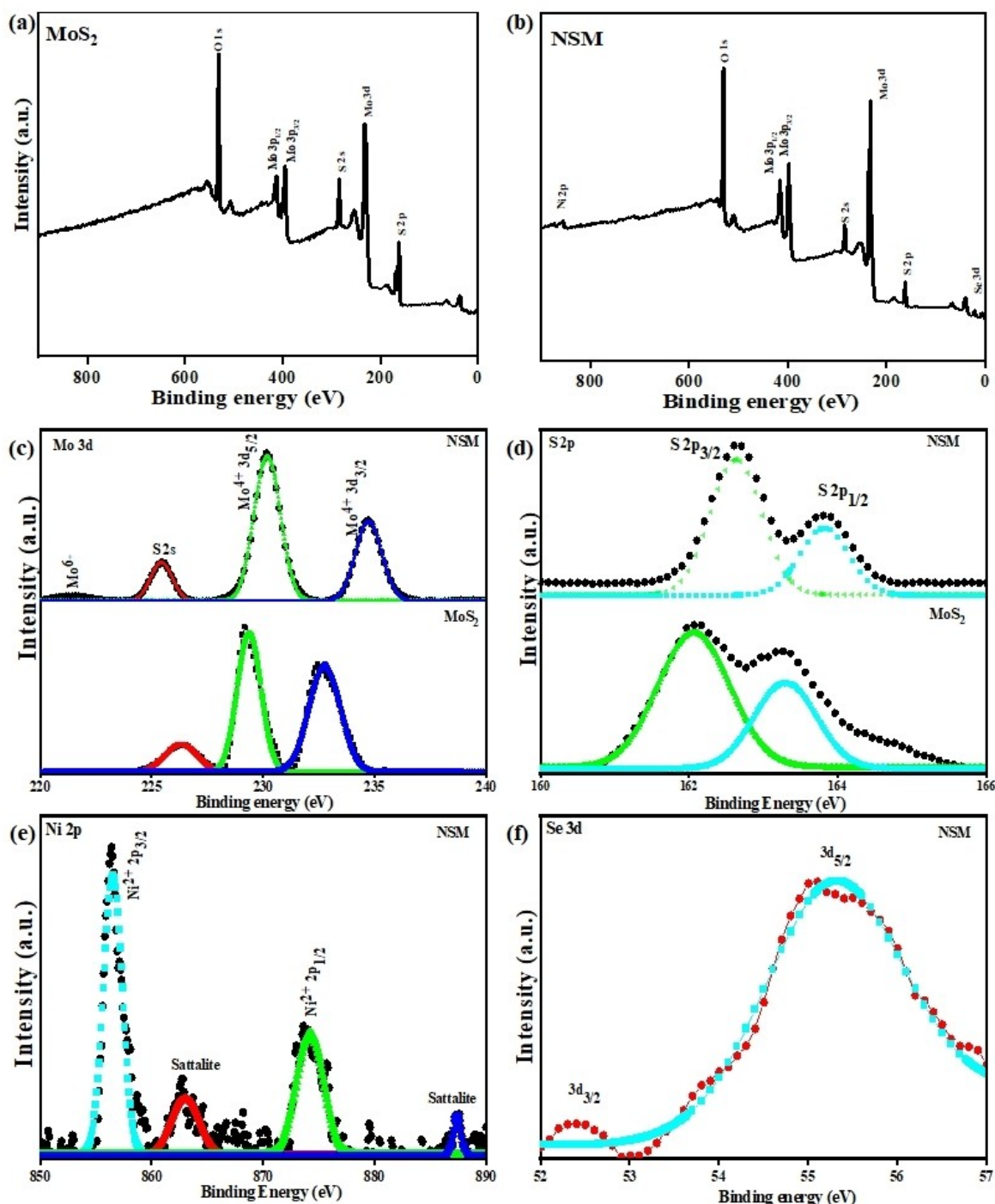


Figure 2. XPS spectra of MoS_2 and $\text{NiSe}_2/\text{MoS}_2$ (a&b) Overall survey (c) High-resolution spectra for Mo 3d (d) High-resolution spectra for S 2p, (e) High-resolution spectra for Ni 2p and (f) High-resolution spectra for Se 3d.

236.1 eV ascribed to Mo^{6+} was observed, signifying a slight oxidation of the Mo edges in $\text{NiSe}_2/\text{MoS}_2$ from the Mo^{4+} to the Mo^{6+} state during the hydrothermal synthesis process. This oxidation can modify the electronic properties and produce more active sites for high catalytic activity for the photocatalytic degradation of pollutants.^[20] The S 2p spectra for MoS_2 and $\text{NiSe}_2/\text{MoS}_2$ (Figure 2d) show the S^{2-} doublet at 162.0 and 163.3 eV and 162.7 and 163.8 eV. The shift to higher binding

energy confirms the observation in the Mo 3d spectra. The Ni 2p spectra of $\text{NiSe}_2/\text{MoS}_2$ (Figure 2e) show four peaks. The peaks at 856.4 and 873.8 eV are attributed to the Ni $2p_{3/2}$ and Ni $2p_{1/2}$ states of Ni^{2+} , while the satellite peaks are observed at 862.8 and 879.7 eV.^[21] The Se 3d spectra (Figure 2f) exhibited a peak at 55.7 eV, which is attributed to the Se^{2-} anion of NiSe_2 .^[22]

Photo(electro)chemical Characterisation

The modulation of charge carrier dynamics constitutes a pivotal determinant in governing the photocatalytic efficacy of a photocatalytic material. Essential charge carrier attributes, including recombination rate, lifetime, and diffusion length, assume paramount significance in the systematic design of nanostructured photocatalysts.^[23] The charge carrier properties of MoS₂ and NiSe₂/MoS₂ were systematically explored using electrochemical impedance spectroscopy (EIS) and current density measurements. Analysis of the EIS spectra unveiled discernible semi-circular arcs, providing valuable insights into the charge carrier transport dynamics and the processes governing the separation and transfer resistance of photo-generated carriers. Figure 3(a) depicts the EIS curve obtained for the MoS₂ and NiSe₂/MoS₂ electrodes, providing insights into the charge transfer mechanisms and charge carrier recombination dynamics inherent to the materials. The observed decrease in the semi-circular arc diameter within the EIS plot signifies a reduction in the charge-transfer resistance occurring at the interface between the electrode and electrolyte.^[24] The EIS curve shows a significant decrease in the semi-circular arc of NiSe₂/

MoS₂ (21.3 Ω), compared to MoS₂ (71.3 Ω) by a factor of 3.5. On this basis, the result indicates that NiSe₂/MoS₂ has a low charge-transfer resistance compared to MoS₂, which signifies effective separation of photoinduced charge carriers across the NiSe₂/MoS₂ surface due to the introduction of NiSe₂. With the low charge transfer resistance, the composite demonstrates an ability to hinder the recombination rate of charge carriers, thereby making them more accessible to participate in PEC activity.^[25] In addition, the improved charge separation and transfer efficiency are key factors in enhancing the photocurrent density of the NiSe₂/MoS₂ materials. To investigate this, the photocurrent density of MoS₂ and NiSe₂/MoS₂ was studied by plotting the current density (I) against potential (V) under illumination and the dark, as shown in Figure 3(b). The current density plot showed that NiSe₂/MoS₂ had a higher current density under illumination and in the dark than MoS₂. The current density of NiSe₂/MoS₂ was almost two times higher than that of MoS₂, showing the importance of NiSe₂ in improving the charge carrier property of MoS₂ sheet. Furthermore, the transient photocurrent response spectra of MoS₂ and NiSe₂/MoS₂ under the intermittent illumination of visible light (Figure 3c) shows that NiSe₂/MoS₂ had the highest photocurrent

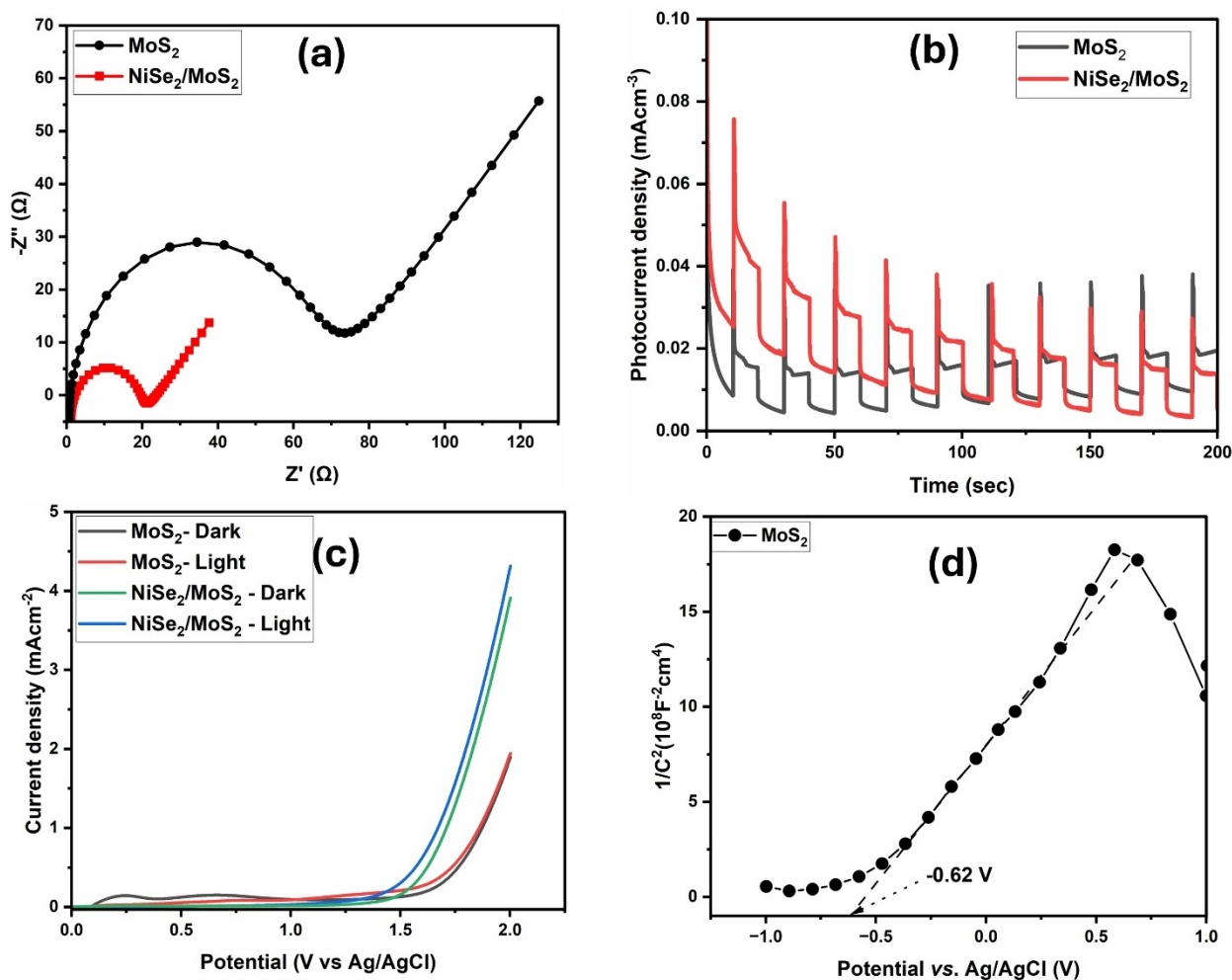


Figure 3. (a) EIS spectra of MoS₂ and NiSe₂/MoS₂, (b) photocurrent density of MoS₂ and NiSe₂/MoS₂, (c) current density of MoS₂ and NiSe₂/MoS₂ in the dark and under illumination and (d) Mott-Schottky plot for MoS₂.

response, indicating that the presence of NiSe₂ promoted charge carrier separation and visible-light response ability.^[26] A spike in the photocurrent response occurred when the light was switched on, inferring the charge separation between the electrolyte and samples. This instantaneous response positively correlates with efficient electron-hole separation, contributing to improved photocatalytic activity.^[27] Both samples displayed a decreasing photocurrent response with time, which could be attributed to hole accumulation.^[28] Without illumination, electron transitions from the semiconductor through the FTO and hole migration in the electrolyte led to a rapid photocurrent loss. Similarly, charge carrier recombination in the semiconductor could also account for the photocurrent loss.^[29] These results demonstrate NiSe₂/MoS₂ superiority over the pristine MoS₂ regarding charge carrier migration and separation.

In Figure 3d, the valence band and conduction band positions of MoS₂ and NiSe₂/MoS₂ were evaluated through the Mott-Schottky (MS) plot. The E-C⁻² plot for the samples showed a positive plot, which suggests n-type semiconductivity.^[30] The flat band potential obtained from the Mott-Schottky plot for MoS₂ was -0.62 eV, and by employing the Nernst equation:

$E_{\text{NHE}} = E_{\text{Ag/AgCl}} + 0.197$, the E_{fb} of MoS₂ is calculated to be -0.42 eV vs NHE, respectively. Generally, n-type semiconductors have conduction bands that are about 0.1–0.2 V, more negative than the E_{fb} .^[31] Therefore, the E_{CB} values for MoS₂ were evaluated to be -0.32 eV vs. NHE. Furthermore, employing the $E_{\text{cb}} = E_{\text{vb}} - E_{\text{g}}$ relation, the valence band (E_{vb}) for MoS₂ was estimated to be 2.04 eV vs NHE.

The optical absorption and electronic properties of pristine MoS₂ and NiSe₂/MoS₂ (Figure 4a) were studied by UV-Vis spectroscopy. The pristine MoS₂ showed broad absorption in the visible region with an absorption edge at around 450 nm. The incorporation of NiSe₂ with MoS₂ in NiSe₂/MoS₂ was observed to enhance the visible light absorption property of NiSe₂/MoS₂. The absorption edge in NiSe₂/MoS₂ shifted to a longer wavelength of ~500 nm, which indicates interfacial charge transfer between MoS₂ and NiSe₂. In addition, the exfoliation of the MoS₂ into few-layered structures could also contribute to the enhanced absorption due to indirect to direct band gap crossover in MoS₂ with few layers.^[16a,32] The Tauc plot was employed in calculating the band gap energy of MoS₂ and

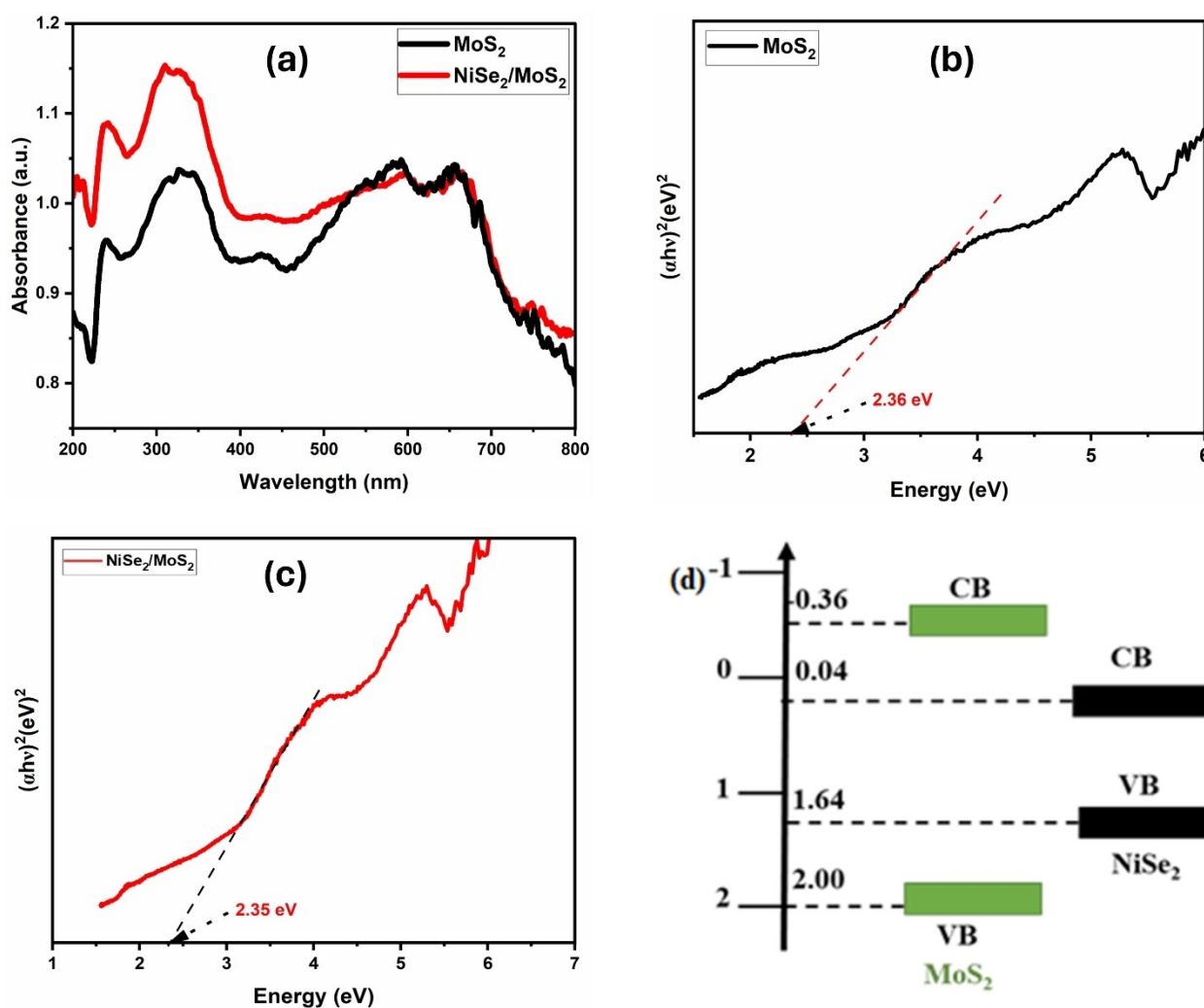


Figure 4. (a) UV-Vis spectra of MoS₂ and NiSe₂/MoS₂, (b&c) Tauc plots for MoS₂ and NiSe₂/MoS₂ and (d) Band alignment for MoS₂ and NiSe₂.

NiSe₂/MoS₂ (Figure 4b&c). The calculated band gap energy for MoS₂ and NiSe₂/MoS₂ are 2.36 eV and 2.35 eV, respectively.

The energies of the E_{CB} and the E_{VB} of the samples can also be theoretically derived from the band gap energy E_g, the energy of the free electrons on the hydrogen scale (E_e 4.5 eV) and the Mulliken electronegativity of the semiconductors X (5.34 eV and 5.32 eV for NiSe and MoS₂, respectively)^[33] according to Eq. 1 & 2:

$$E_{vb} = X - E^e + 0.5E_g \quad (1)$$

$$E_{cb} = E_{vb} - E_g \quad (2)$$

From the calculation, the E_{CB} potential of MoS₂ (-0.36 eV) is higher compared to that of NiSe₂ (0.04 eV), while the E_{VB} of MoS₂ (2.00 eV) is lower compared to that of NiSe₂ (1.6 eV). This confirms the nesting of the NiSe₂ band gap by that of MoS₂, as shown in Figure 4d.

Degradation studies

The photoelectrocatalytic activities of MoS₂ and NiSe₂/MoS₂ photoanodes were investigated for the degradation of CIP for 120 mins. The efficiency of the process was monitored by measuring the absorbance of the aliquots taken from the solution at regular intervals. For pristine MoS₂, the photoanode achieved approximately 35% (0.0047 min⁻¹), while a significantly enhanced 78% (0.0111 min⁻¹) degradation efficiency was achieved by NiSe₂/MoS₂ photoanode under the same condition (Figure 5a&b). This shows the significant improvement in PEC activity induced by heterojunction formation between MoS₂ and NiSe₂. To determine the synergy between photocatalysis and electrocatalysis, the degradation efficiency of CIP was evaluated for the individual process (Figure 5c&d). The degradation efficiency was 20% (0.00146 min⁻¹) and 57% (0.00408 min⁻¹) for photocatalysis and electrocatalysis, respectively. To estimate this synergy between the two processes, the synergistic effect (S), which is the ratio of the rates observed in the hybrid process to the sum of the rates of the individual

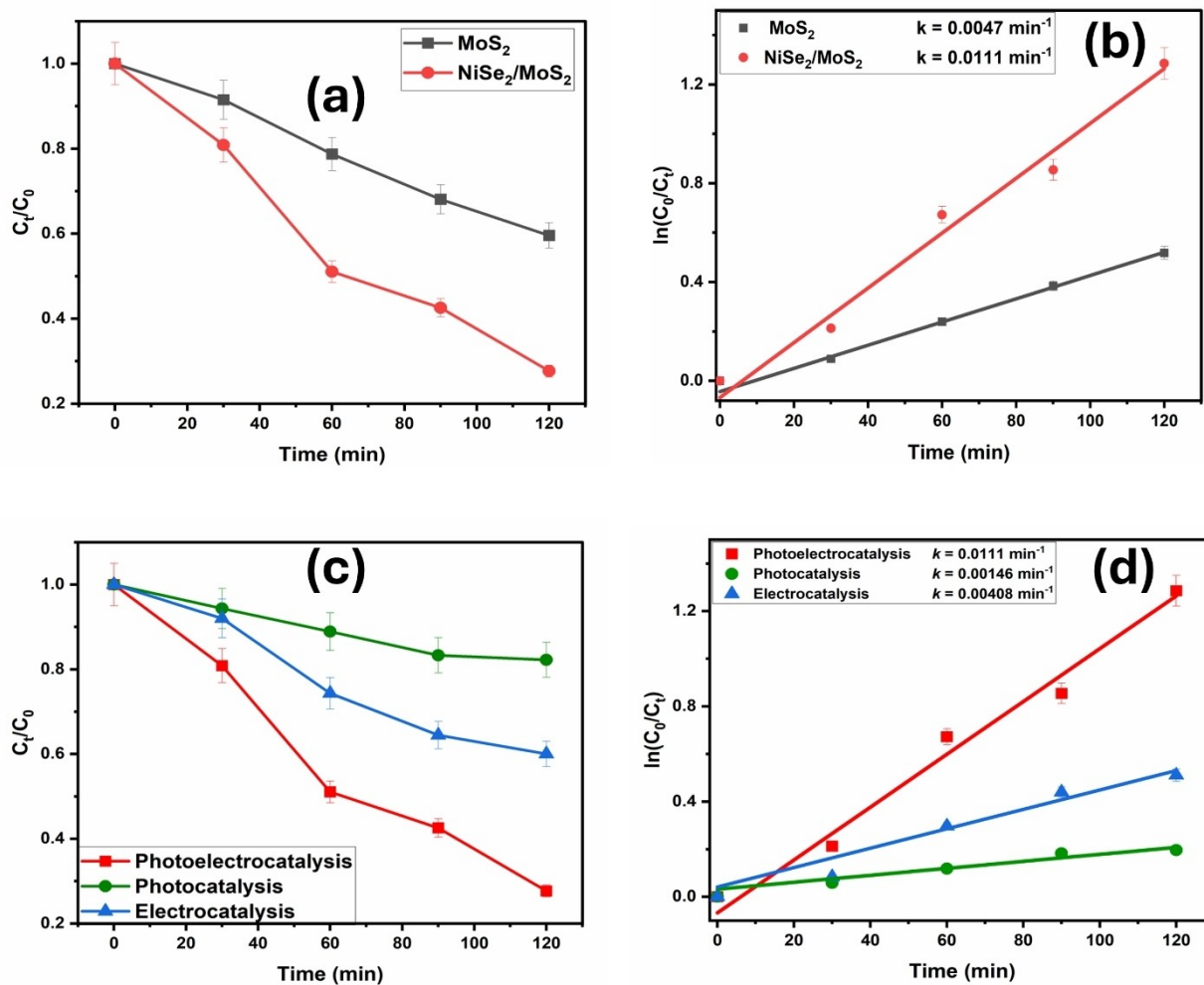


Figure 5. (a) Photoelectrocatalytic degradation profile of CIP by MoS₂ and NiSe₂/MoS₂ (b) First order kinetic plot for CIP degradation by MoS₂ and NiSe₂/MoS₂ (c) Degradation profile of CIP by NiSe₂/MoS₂ in photo electrocatalytic, photocatalytic and electrocatalytic processes and (d) First order kinetic plot of photo electrocatalytic, photocatalytic and electrocatalytic degradation of CIP.

process, was evaluated.^[34] The value of S for the PEC process using $\text{NiSe}_2/\text{MoS}_2$ photoanode was 2.00, showing a strong synergy between the two processes. Furthermore, a comparison of CIP degradation by $\text{NiSe}_2/\text{MoS}_2$ photoanode with other MoS_2 -based materials (Table 1) showed its activity is on par with them.

Five catalytic treatment cycles were evaluated for CIP degradation to investigate the $\text{NiSe}_2/\text{MoS}_2$ photoanode's stability. The $\text{NiSe}_2/\text{MoS}_2$ showed strong stability with only a slight reduction after five cycles (Figure 6a). Furthermore, the roles of radical species: superoxides ($\text{O}_2^{\bullet-}$), holes (h^+) and hydroxyl ($\cdot\text{OH}$) radical were investigated by introducing radical scavenging species, triethanol amine (TEA), ethylene diamine (EDTA-Na) and isopropanol (IPA) into the system. Figure 6b shows a reduction in the efficiency of the PEC process by 7%, 11% and 59% on introducing IPA, TEA and EDTA, respectively. This shows that h^+ played the most significant role in the catalytic activity of $\text{NiSe}_2/\text{MoS}_2$, while $\text{O}_2^{\bullet-}$ and $\cdot\text{OH}$ only played minor roles.

Photoelectrocatalytic Degradation Mechanism of CIP by $\text{NiSe}_2/\text{MoS}_2$

The band alignment scheme presented earlier shows the straddling of the band structure of NiSe_2 within that of MoS_2 , which seems unfavourable for enhanced catalytic activity prior to the formation of the heterostructure. However, with the formation of the n-n heterojunction, a charge redistribution of NiSe_2 and MoS_2 occurs at the materials' interface. The flow of

electrons is usually from the material with the higher Fermi level (E_F) to the one with the lower Fermi level. It continues until there is an equilibration of the E_F levels. The Fermi energy level of MoS_2 (4.57 eV)^[39] and NiSe_2 (4.52 eV)^[40] implies that the flow of electron is from MoS_2 to NiSe_2 , which leads to the downward movement of the energy band positions of MoS_2 towards positive potential and those of NiSe_2 move up to more negative potential.^[41] Furthermore, photoinduced charge carriers are generated by the promotion of electrons from the valence band of both MoS_2 and NiSe_2 into the valence band. Due to the n-n heterojunction at the interface, the built-in electric field drives the transfer of excited electrons from the CB of MoS_2 and combines with the holes in the VB of NiSe_2 . Under the applied external potential, the electrons on the CB of NiSe_2 migrate to the counter electrode, with the holes on the VB of MoS_2 available for the degradation of CIP. This proposed charge transfer mechanism in $\text{NiSe}_2/\text{MoS}_2$ heterojunction (Figure 7) agrees with the radical scavenging experiments and accounts for the high synergy between the photocatalytic and electrocatalytic processes.

Conclusions

The $\text{NiSe}_2/\text{MoS}_2$ heterostructure has been successfully fabricated by a facile solvothermal method and confirmed by characterization techniques such as XRD, SEM, TEM and XPS analysis. The study comprehensively explored the photoelectrocatalytic (PEC) performance of the $\text{NiSe}_2/\text{MoS}_2$ heterojunction in ciprofloxacin

Table 1. Comparison of CIP degradation by previously reported MoS_2 -based heterojunction photocatalyst.

Catalysts	Process	Catalyst Dosage	CIP	Degradation	Rate constant	Ref.
$\text{Fe}_3\text{CN@MoS}_2$ -4	Photo-assisted peroxymonosulfate	30 mg	10 mg/L, 100 mL, 140 min.	83 %	0.0052 min^{-1}	[35]
MoS_2/ZnO	Photocatalysis	50 mg	0.05 M, 100 mL, 120 min	89 %	0.014 min^{-1}	[36]
$\text{MoS}_2/\text{CoTiO}_3$	Photocatalysis	50 mg	20 ppm, 50 mL, 90 min	82 %	0.0279 min^{-1}	[37]
$\text{MoS}_2/\text{PbBiO}_2\text{I}$	Photocatalysis	30 mg	10 mg/L, 100 mL, 120 min	84 %	–	[38]
$\text{MoS}_2/\text{NiSe}_2$	Photoelectrocatalysis	50 mg	5 mg/L, 100 mL, 120 min	78 %	0.0111	This study

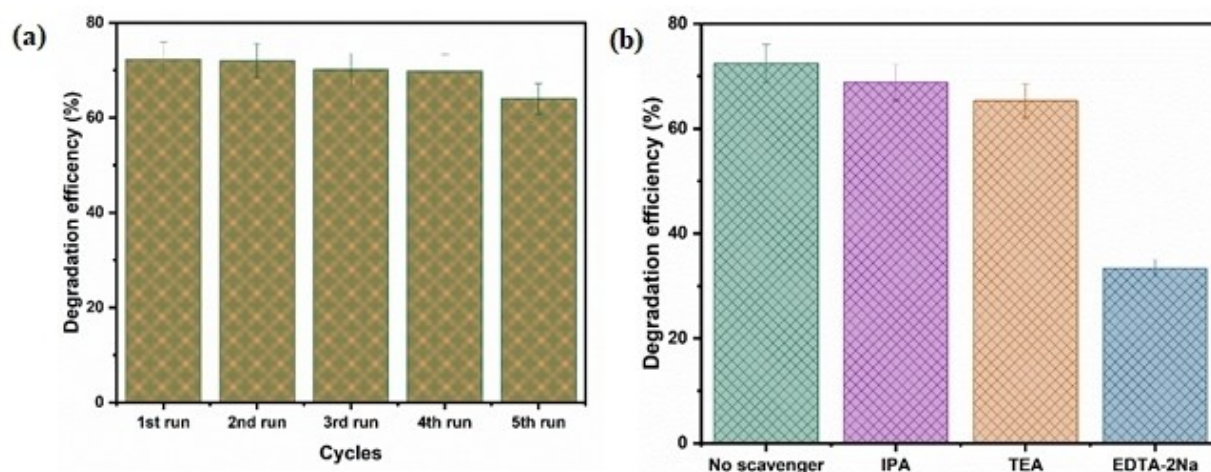


Figure 6. (a) 5-cycle stability test for $\text{NiSe}_2/\text{MoS}_2$ and (b) Radical scavenging experiment for PEC degradation of CIP.

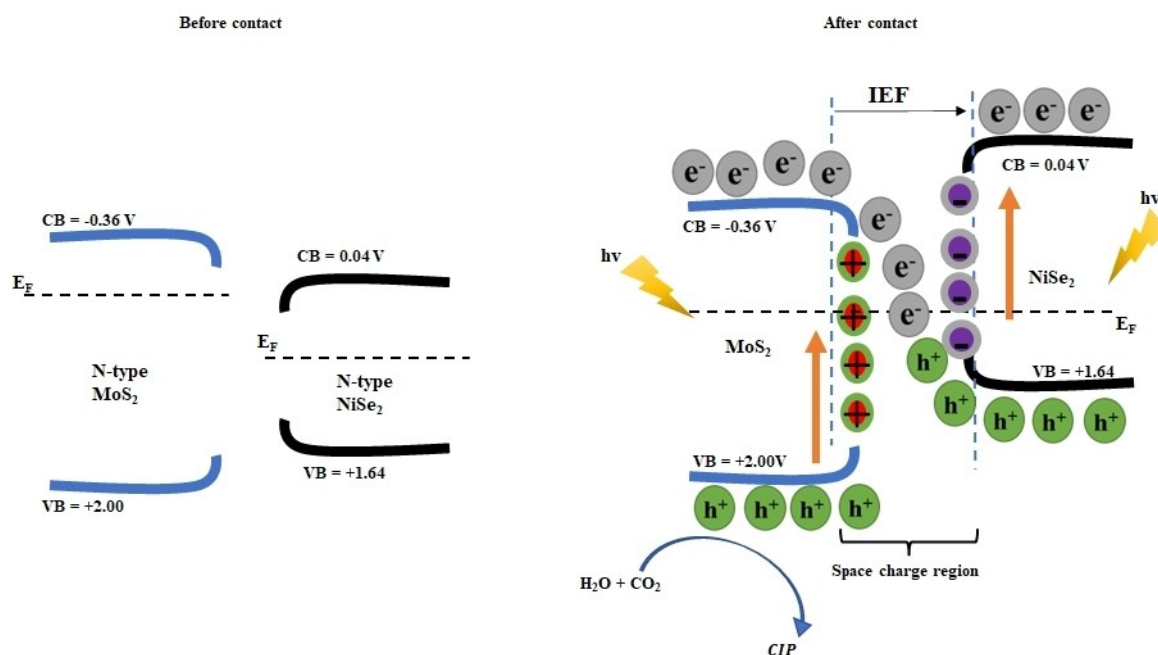


Figure 7. Proposed mechanism for the PEC degradation of CIP.

(CIP) degradation, a prevalent antibiotic contaminant. Our findings demonstrate that the NiSe₂/MoS₂ heterojunction significantly enhances PEC activity, achieving a degradation efficiency of approximately 78%, notably surpassing the 38% efficiency exhibited by MoS₂ alone. This improvement is largely attributed to the effective charge redistribution and realignment of band structures at the n–n interface, facilitating better charge carrier separation and utilization under the influence of visible light and an external electric field. Additionally, the stability and reusability tests of the NiSe₂/MoS₂ composite indicate no substantial loss in activity over five cycles, underscoring its potential for long-term application in water treatment processes. By further mechanistic investigation, parameter optimization, and pilot scale, we can further harness the potential of n–n heterojunctions like NiSe₂/MoS₂ in environmental remediation, particularly in the efficient and sustainable removal of hazardous pharmaceuticals from wastewater.

Experimental

Materials

Nickel chloride hexahydrate (NiCl₂·6H₂O), sodium selenite (Na₂SeO₃), ethylene glycol (EG), Molybdenum disulfide (MoS₂) ciprofloxacin (CIP), acrylamide, Polyvinylidene fluoride, *N*-methyl-2-pyrrolidone, sodium sulfate (Na₂SO₄), disodium salt of ethylenediaminetetraacetate (Na₂EDTA), tert-butanol (t-BuOH), acrylamide, potassium tetraoxomanganate (VII) (KMnO₄), potassium hexacyanoferrate (II) (K₄Fe(CN)₆) and potassium hexacyanoferrate (III) (K₃Fe(CN)₆). No further purification was carried out on all the chemicals obtained from Sigma-Aldrich (South Africa).

Synthesis of NiSe₂/MoS₂

The NiSe₂/MoS₂ synthesis was achieved through the in-situ deposition of NiSe₂ onto MoS₂. Initially, 1.0 mmol of MoS₂ was dispersed in ethylene glycol and subjected to ultrasonication for 1 hour. Afterward, a solution containing NiCl₂·6H₂O (0.025 mmol) and Na₂SeO₃ (0.05 mmol) was added and sonicated for 30 minutes. The mixture was then transferred into a 100 mL Teflon-lined autoclave and placed in a muffle furnace at 180 °C for 24 hours. Subsequently, the solution was allowed to cool naturally, and the residue was collected, washed three times with ethanol and water, and dried in an oven at 70 °C for 12 hours to obtain NiSe₂/MoS₂.

Characterization

A Rigaku Ultima IV X-ray diffractometer (XRD) sourced from Japan was used to discern the crystalline phases within the composite and pristine samples. The X-ray radiation source employed was Cu K α ($\lambda = 1.5406 \text{ \AA}$), enhanced with a K- β filter, operating at 30 mA and 40 kV. To examine the shapes and constituent elements of the samples, a Field Emission Scanning Electron Microscope (FE-SEM), specifically the Zeiss Crossbeam 540 model from the United Kingdom, was employed, coupled with Energy Dispersive X-ray Spectroscopy (EDS). High-resolution images were captured using a JEM-2100 transmission electron microscope (TEM) from Japan. Electronic absorption spectra were collected using a Cary 60 UV-vis spectrometer manufactured by Agilent Technologies in Malaysia. Electrochemical impedance spectroscopy, Mott Schottky analysis, and photocurrent response measurements were conducted utilising an Autolab Potentiostat workstation (PGSTAT204) from the Netherlands. The photoluminescence spectra were recorded on Shimadzu spectrofluorophotometer RF-6000.

Fabrication of Photoanode

To construct the photoanode, Fluorine-doped tin oxide (FTO) was used as the base for electrode production. The catalysts were applied to the substrate using the drop-casting method. Initially, the FTO glass was cleaned by sonication in acetone for 10 minutes, followed by a rinse with water and drying at 60 °C. For the catalyst dispersion, 100 μ L of N-methyl-2-pyrrolidone and 5 mg of polyvinylidene fluoride were combined with 50 mg of each MoS₂ and NiSe₂/MoS₂ sample and stirred continuously to form a uniform slurry. The slurry was then carefully spread over the conductive surface of the FTO glass, measuring 1.7 cm by 1.7 cm, to ensure an even layer. After application, the coated glass was dried in an oven at 60 °C for 2 hours.

Photoelectrochemical Study

The PEC (photoelectrochemical) studies utilized a traditional three-electrode cell setup, which included a Pt wire as the counter electrode, an Ag/AgCl (in 3.0 M KCl) as the reference electrode, and the specially designed photoanode serving as the working electrode. Illumination was provided by a 100 W xenon solar lamp. The incident light source and the photoanode were arranged vertically, maintaining a 10 cm distance between them. The electrolyte used for the impedance spectroscopy analysis was a solution of 5 mM [Fe(CN)₆]³⁻/[Fe(CN)₆]⁴⁻ in 0.1 M KCl, with an applied potential of +0.25 V, conducted without light at frequencies ranging from 100 kHz to 0.1 Hz. The impedance spectroscopy (EIS) data were analyzed using a Randles circuit model. Mott-Schottky measurements were taken in darkness, using an electrolyte solution of 5 mM [Fe(CN)₆]^{3/4-} in 0.1 M KCl. For photocurrent level assessment, a 0.1 M Na₂SO₄ solution was employed. The degradation process of CIP was carried out in a 100 mL quartz glass container.

Degradation of Ciprofloxacin (CIP)

The degradation of CIP was carried out in a quartz glass container with a capacity of 100 mL with a bias potential of 1.2 V. The electrolyte solution consisted of 5 mg/L CIP dissolved in 0.1 M Na₂SO₄. To examine the impact of electrolysis on the degradation process, the experiment was replicated without exposure to light. The degradation progress was monitored by measuring the absorbance of the CIP sample at 30 min intervals using a UV-vis spectrophotometer.

Conflict of Interests

The authors declare no conflict of interest.

Data Availability Statement

The data that support the findings of this study are available from the corresponding author upon reasonable request.

Keywords: photoelectrocatalytic degradation · n-n heterojunction · ciprofloxacin · pharmaceutical

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